

MOS FET FKV460S

絶対最大定格

(Ta=25°C)

記号	規格値	単位
V _{DSS}	40	V
V _{GSS}	+20, -10	V
I _D	±60	A
I _{D(pulse)} *	±180	A
P _D	60 (T _c =25°C)	W
T _{ch}	150	°C
T _{stg}	-55~+150	°C

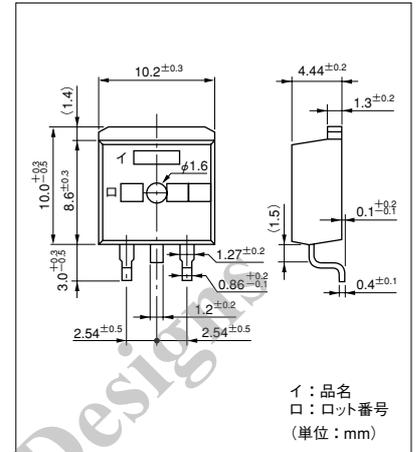
*P_W≤100μs, duty≤1%

電気的特性

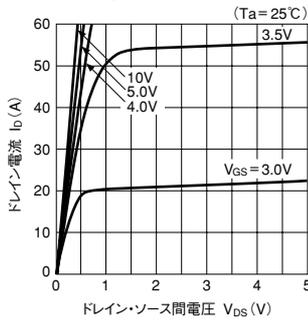
(Ta=25°C)

記号	試験条件	規格値			単位
		min	typ	max	
V _{(BR)DSS}	I _D =100μA, V _{GS} =0V	40			V
I _{GSS}	V _{DS} =+20V V _{GS} =-10V		+10	-5	μA
I _{DSS}	V _{DS} =40V, V _{GS} =0V			100	μA
V _{TH}	V _{DS} =10V, I _D =250μA	1.0		2.5	V
R _{e(yf)}	V _{DS} =10V, I _D =25A	20			S
R _{DS(ON)}	V _{GS} =10V, I _D =25A		7	9	mΩ
C _{iss}	V _{DS} =10V f=1.0MHz		2800		pF
C _{oss}			1400		pF
C _{rss}	V _{GS} =0V		600		pF
t _{d(on)}	I _D =25A		20		ns
t _r	V _{DD} =12V R _L =0.48Ω		600		ns
t _{d(off)}			250		ns
t _f	V _{GS} =10V		100		ns
V _{SD}	I _{SD} =50A, V _{GS} =0V	1.0		1.5	V

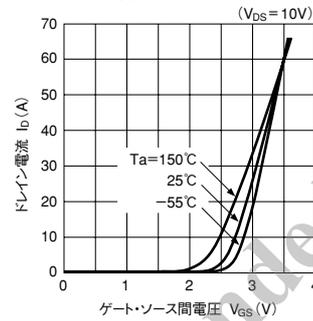
外形図 TO220S



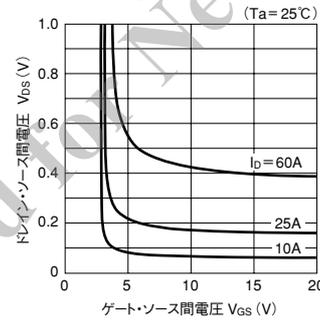
■ I_D-V_{DS} 特性 (代表例)



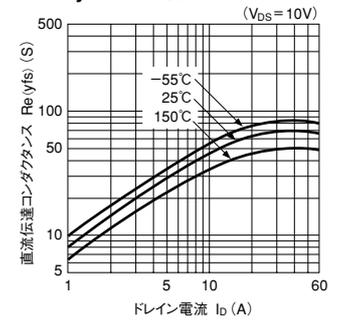
■ I_D-V_{GS} 特性 (代表例)



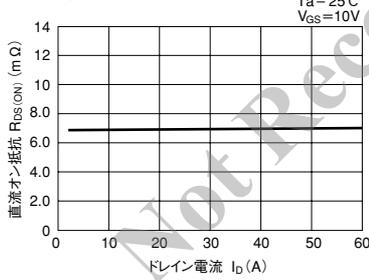
■ V_{DS}-V_{GS} 特性 (代表例)



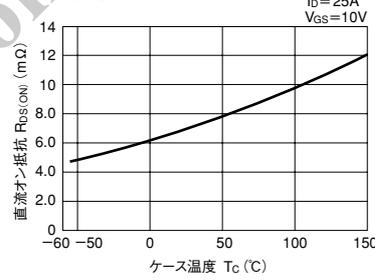
■ R_{e(yf)}-I_D 特性



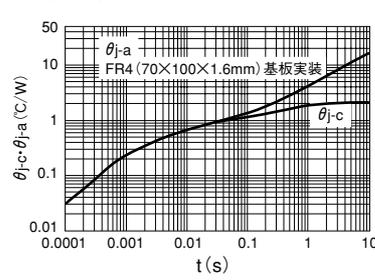
■ R_{DS(ON)}-I_D 特性



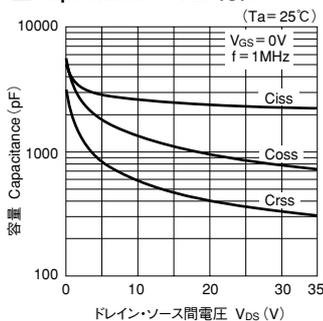
■ R_{DS(ON)}-T_C 特性



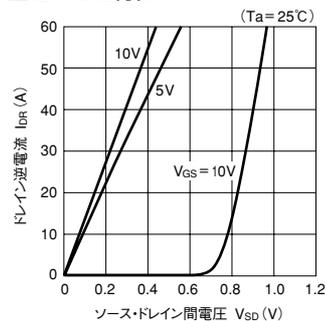
■ θ_{j-c}·θ_{j-a}-t 特性 (単発パルス)



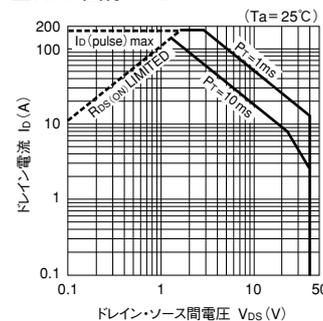
■ Capacitance-V_{DS} 特性



■ I_{DR}-V_{SD} 特性



■ ASO 曲線 (単発パルス)



■ P_D-T_C 特性

